

MICRO

ELECTRONICS

查询MI51TA代理商

捷多邦, 专业PCB打样工厂, 24小时加急出货

MI51TA
MIB51TA
INFRARED
EMITTING
DIODE

DESCRIPTION

MI51TA & MIB51TA are GaAlAs infrared emitting diode molded T-1 3/4 standard 5mm diameter clear plastic package, with the lensing effect of the package, and MIB51TA with cup type leadframe.

ABSOLUTE MAXIMUM RATINGS

Forward Current (Continuous)	100mA
Pulse Forward Current	1A*
Reverse Voltage (Continuous)	6V
Power Dissipation	180mW
Operating Temperature Range	-25 to +85°C
Lead Soldering Temperature (1/16" from body)	260°C for 5 sec.

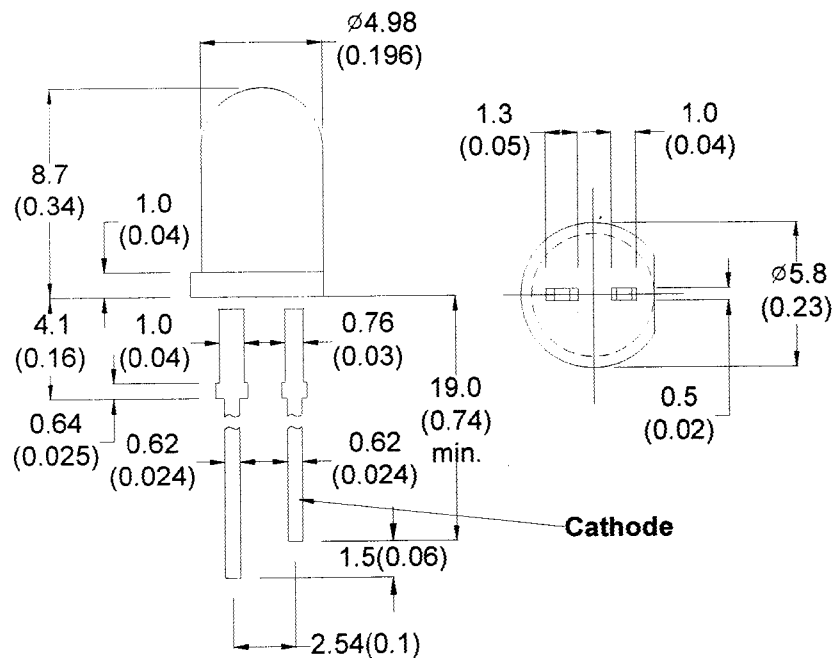
* Pulse Width = 10 μ s, Duty Ratio = 0.01.

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER		SYMBOL	MI51TA	MIB51TA	UNIT	CONDITIONS
Radiant Power Output	TYP	Po	5	8	mW	IF=50mA
Forward Voltage	MAX	V _F	1.8	1.8	V	IF=20mA
Reverse Current	MAX	I _R	100	100	μ A	VR=5V
Half Intensity Beam Angle	TYP	θ HI	40	70	degree	IF=20mA
Peak Wavelength	TYP	λ p	880	880	nm	IF=20mA
Spectrum Line Half Width	TYP	$\Delta \lambda$	70	70	nm	IF=20mA

MECHANICAL OUTLINE

MI51TA



MIB51TA

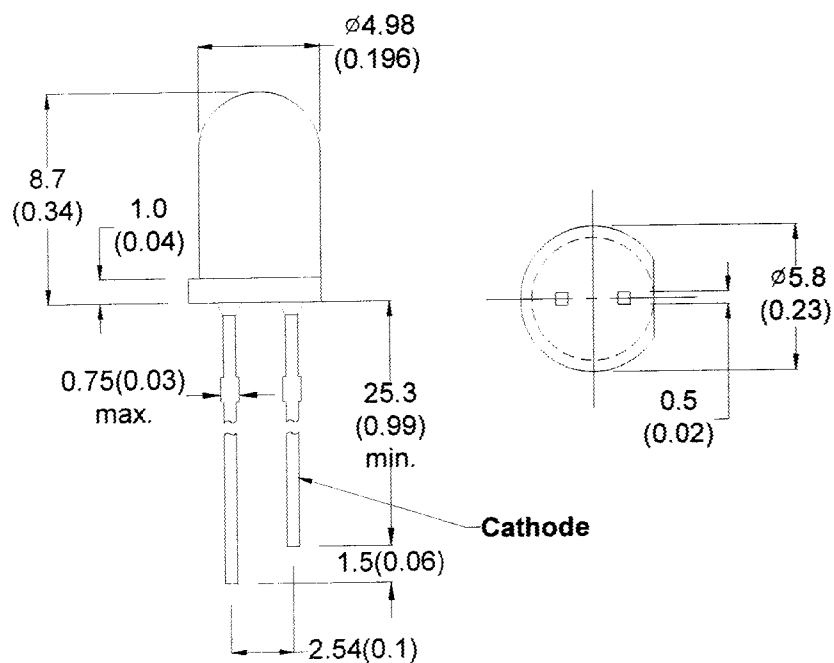


FIGURE 12

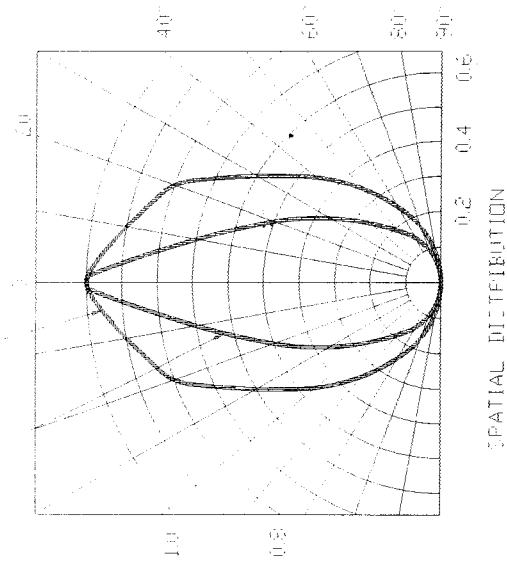


FIGURE 13

